●Feature

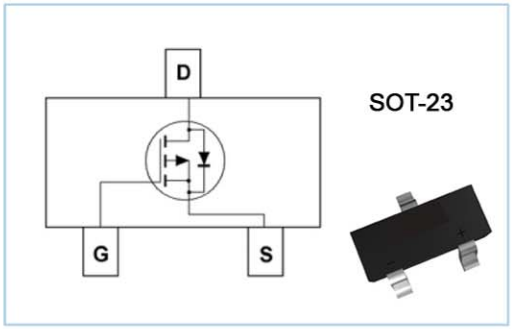
-16V/-3A, $R_{DS(ON)}$ = 160mΩ (MAX) @V_{GS} = -4.5V.

$R_{DS(ON)}$ = 240mΩ (MAX) @V_{GS} = -2.5V.

Super High dense cell design for extremely low $R_{DS(ON)}$

Reliable and Rugged

SOT-23 for Surface Mount Package



●Applications

Power Management

Portable Equipment and Battery Powered Systems.

●Absolute Maximum Ratings

T_A=25℃ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current-Continuous	I_D	-3	A

●Electrical Characteristics

T_A=25℃ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=-12V, VGS=0V	-	-	-5	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=8V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-8V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250μA	-0.45	-	-1.5	V
Static Drain-source On-Resistance	RDS(ON)	VGS =-4.5V, ID =-3.0A	-	-	160	mΩ
		VGS =-2.5V, ID =-2.0A	-	-	240	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.25A			-1.8	V

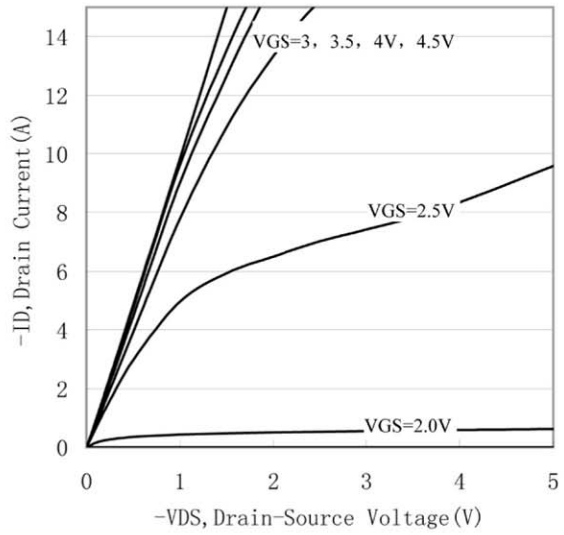


Figure 1. Output Characteristics

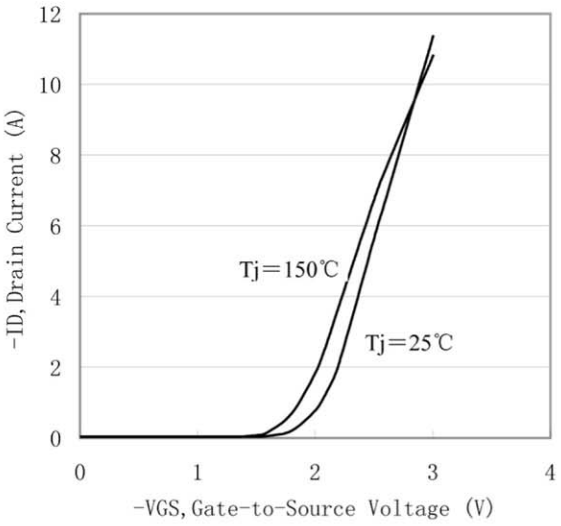


Figure 2. Transfer Characteristics

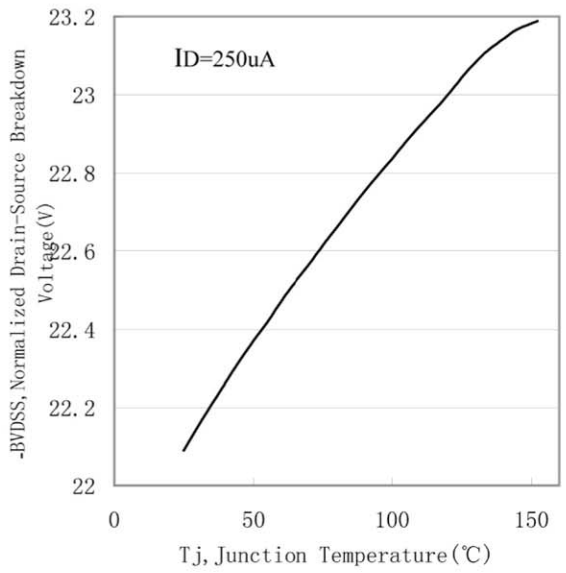


Figure 3. Breakdown Voltage Variation with Temperature

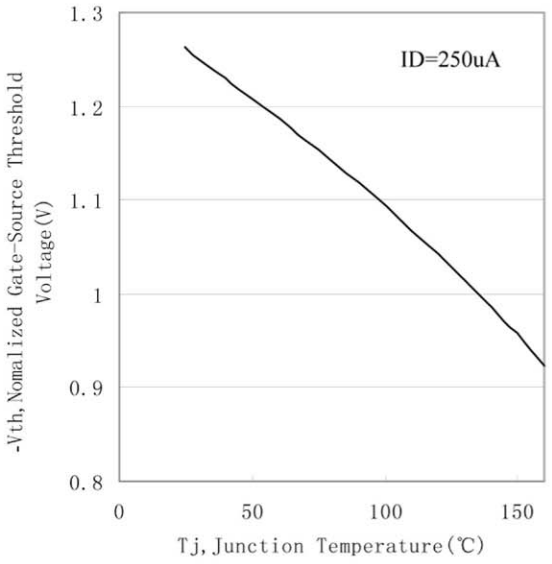


Figure 4. Gate Threshold Variation with Temperature

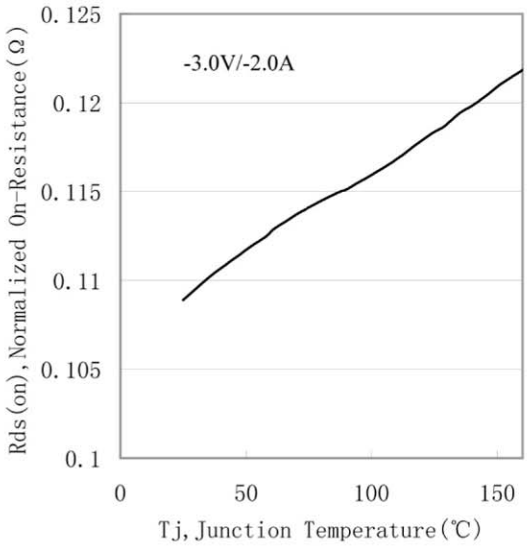


Figure 5. On-Resistance Variation with Temperature

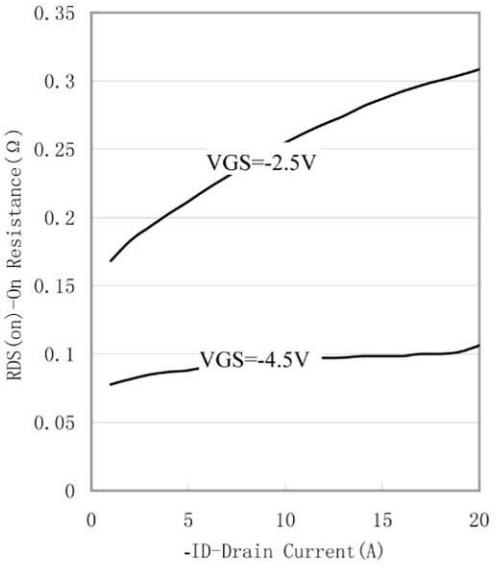


Figure 6. On-Resistance vs. Drain Current

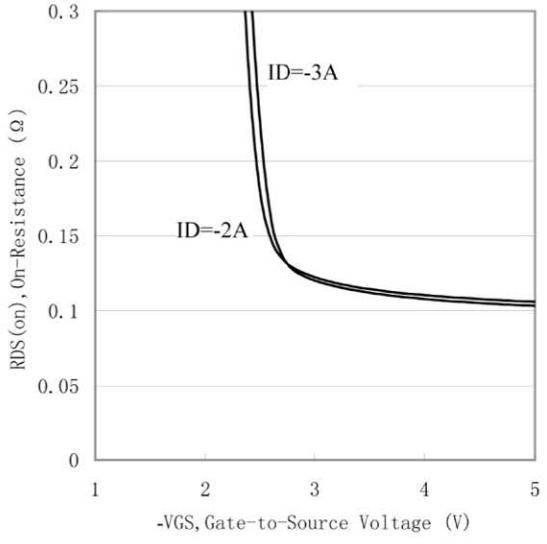


Figure 7. On-Resistance vs. Gate-to-Source Voltage

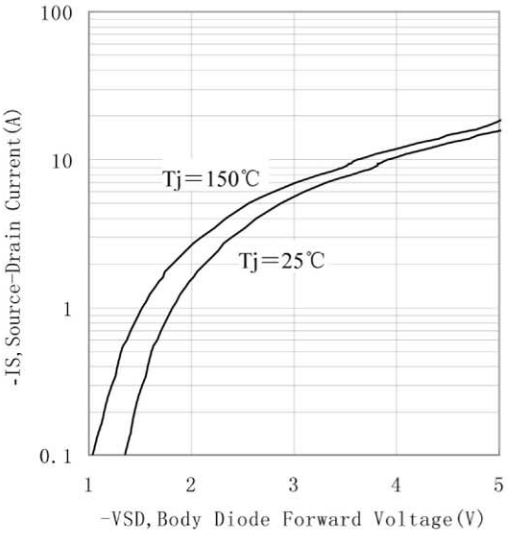


Figure 8. Source-Drain Diode Forward Voltage